

**Amendments to the Claims:**

1. **(Currently Amended)** A semiconductor device comprising:  
a semiconductor element that has a first surface on which an external connection terminal is formed and a second surface ~~that faces~~ opposite the first surface, and a thickness of 10 $\mu$ m or more and 150 $\mu$ m or less;  
a plate that faces the second surface; and  
a resin binder that adheres the second surface and the plate,  
wherein the plate has a rigidity higher than that of the semiconductor element;  
wherein the second surface of the semiconductor element comprises a surface-finished surface such that the second surface of the semiconductor element is free from having a damaged layer thereon;  
wherein an outer shape of the plate is larger than that of the semiconductor element; and  
wherein the resin binder covers a peripheral side face of the semiconductor element, and  
furthermore at a portion that is interposed between the second surface and the plate the resin binder allows the semiconductor element to deform in a thickness direction thereof.
2. **(Previously presented)** The semiconductor device according to claim 1, wherein the resin binder covers at least an edge defined by a side face and the second surface of the semiconductor element, about the outer periphery of the semiconductor element.
3. **(Previously presented)** The semiconductor device according to claim 1, wherein the resin binder covers the side face over an entire circumference of the semiconductor element.
4. **(Previously presented)** The semiconductor device according to claim 1, wherein the resin binder covers only a corner of the side face of the semiconductor element.

5. **(Canceled)**

6. **(Original)** The semiconductor device according to claim 1, wherein the external connection terminal is provided with a bump.

Claims 7 and 8. **(Cancelled)**

9. **(Previously presented)** The semiconductor device according to claim 1, wherein the semiconductor element includes a re-wiring layer on the first surface, the re-wiring layer has a surface electrode formed on a surface and an internal electrode formed inside thereof, and the internal electrode connects the surface electrode and the external connection terminal.

10. **(Original)** The semiconductor device according to claim 9, wherein the surface electrode is provided with a bump.

11. **(Previously presented)** A semiconductor device assembling method in which a semiconductor element and a plate that is higher in rigidity than the semiconductor element are adhered via a resin binder, the semiconductor element having a first surface on which an external connection terminal is formed and a second surface opposite the first surface, the second surface being adhered to the plate, said method comprising:

roughly processing by mechanically polishing a side opposite to the first surface on which an external connection terminal of the semiconductor element is formed, followed by further applying finishing to obtain a second surface from which a damaged layer is removed and to make a thickness of the semiconductor element 10 $\mu$ m or more and 150 $\mu$ m or less;

supplying the resin binder to a plate member including the plate;

adhering the second surface and the plate in an aligned state by use of the resin binder;

and

cutting the plate from the plate member.

12. **(Previously presented)** The semiconductor device assembling method according to claim 11, wherein, in said adhering, the resin binder is formed to cover an outer periphery of the semiconductor element.

13. **(Previously presented)** The semiconductor device assembling method according to claim 12, wherein, in said adhering, the resin binder is spread to a side face of the semiconductor element to cover the outer periphery by decreasing the viscosity of the resin binder by heating.

14. **(Previously presented)** The semiconductor device assembling method according to claim 11, wherein said supplying comprises supplying the resin binder by an amount necessary to cover a side face of the semiconductor element.

15. **(Previously presented)** The semiconductor device assembling method according to claim 11, wherein, in said supplying, the resin binder supplied is liquid resin, the plate member has a projection surrounding the plate, and the liquid resin is supplied inside of the projection.

16. **(Previously presented)** The semiconductor device assembling method according to claim 11, wherein, in said supplying, the resin binder is supplied as a resin binder sheet, and the resin binder sheet is adhered to the plate member.

17. **(Previously presented)** The semiconductor device assembling method according to claim 11, wherein  
said plate constitutes one of a plurality of plates;  
said semiconductor element constitutes one of a plurality of semiconductor elements; and

said adhering includes mounting the semiconductor elements via the resin binder for each of the plates of the plate member, and heating the plate member on which the semiconductor elements are mounted.

18. **(Previously presented)** The semiconductor device assembling method according to claim 17, wherein, in said adhering, said mounting and said heating are carried out simultaneously.

19. **(Previously presented)** The semiconductor device assembling method according to claim 18, wherein said adhering is carried out by use of a semiconductor element mounting device that includes a heating device.

20. **(Original)** The semiconductor device assembling method according to claim 11, wherein the semiconductor element has a re-wiring layer on the first surface.

21. **(New)** The semiconductor device according to claim 1, wherein a surface of the peripheral side face of the semiconductor element includes a micro crack, and the resin binder covering the peripheral side face of the semiconductor element reinforces the peripheral side face having the micro crack.

22. **(New)** The semiconductor device according to claim 1, wherein the first surface of the semiconductor element is exposed from the resin binder.